优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Product Summary

BV_{DSS}	$R_{DS(ON)\ MAX}$	$I_{D\ MAX}$ T_A = +25°C
30V	38mΩ @ V_{GS} = 10V	5.8A
	64mΩ @ V_{GS} = 4.5V	4.5A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load Switch
- DC-DC Converters
- Power Management Functions

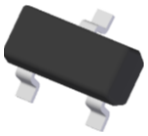
Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage

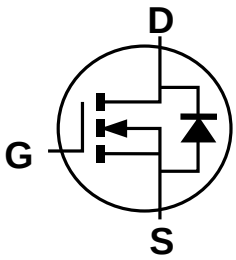
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

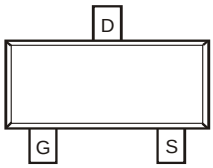
SOT23



Top View



Equivalent Circuit



Top View
Pin-Out

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C	I_D	4.5	A
		T_A = +70°C		3.5	
	t<5s	T_A = +25°C	I_D	5.8	A
		T_A = +70°C		4.9	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	20	A
Maximum Body Diode Forward Current (Note 6)			I_S	2	A

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	0.7	W
	T_A = +70°C		0.44	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	182	°C/W
	t < 5s		109	
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	1.4	W
	T_A = +70°C		0.85	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	94	°C/W
	t < 5s		56	
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	25	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	800	nA	V_{DS} = 28V, V_{GS} = 0V
Gate-Body Leakage	I_{GSS}	—	—	±80	nA	V_{GS} = ±12V, V_{DS} = 0V
				±800		V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.3	1.9	2.2	V	V_{DS} = V_{GS}, I_D = 250 µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	33	38	mΩ	V_{GS} = 10V, I_D = 5.8A
			54	64		V_{GS} = 4.5V, I_D = 5.0A
Forward Transconductance	$\|Y_{fs}\|$	—	5	—	s	V_{DS} = 5V, I_D = 3.1A
Source-Drain Diode Forward Voltage	V_{SD}	—	0.78	1.16	V	V_{GS} = 0V, I_S = 2.0A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	424	—	pF	V_{DS} = 5V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	115	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	81	—	pF	
Gate Resistance	R_g	—	1.51	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_g	—	9.0	—	nC	V_{GS} = 10V, V_{DS} = 15V, I_D = 5.8A
Gate-Source Charge	Q_{gs}	—	1.3	—	nC	
Gate-Drain Charge	Q_{gd}	—	1.3	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	3.4	—	ns	V_{DD} = 15V, V_{GS} = 10V, R_L = 2.6Ω, R_g = 3Ω
Turn-On Rise Time	t_R	—	6.2	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	13.9	—	ns	
Turn-Off Fall Time	t_F	—	2.8	—	ns	

Notes: 5. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2 oz. Copper, single sided.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

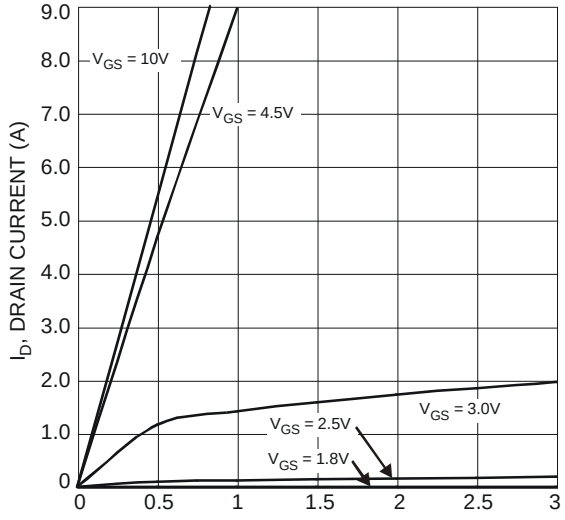


Fig. 1 Typical Output Characteristics

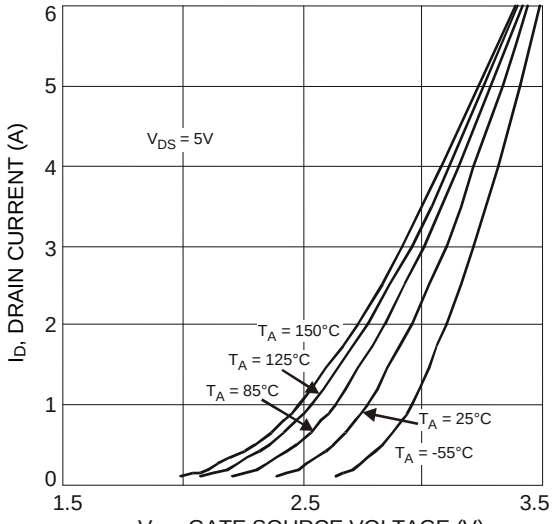


Fig. 2 Typical Transfer Characteristics

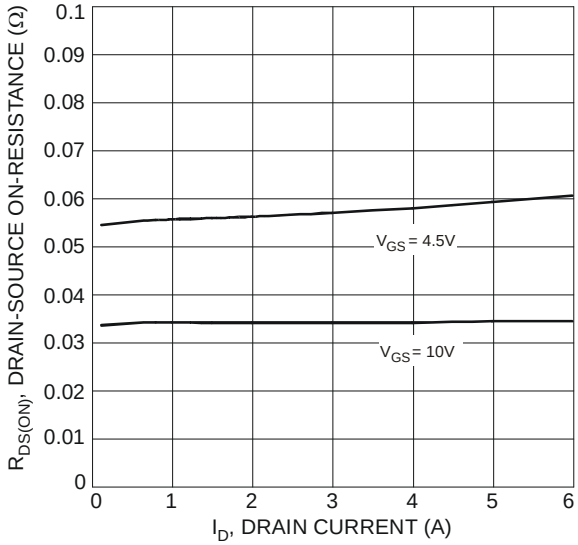


Fig. 3 Typical On-Resistance
vs. Drain Current and Gate Voltage

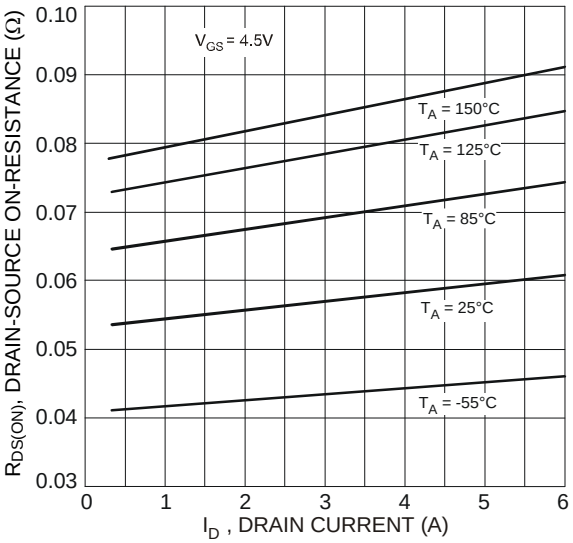


Fig. 4 Typical Drain-Source On-Resistance
vs. Drain Current and Temperature

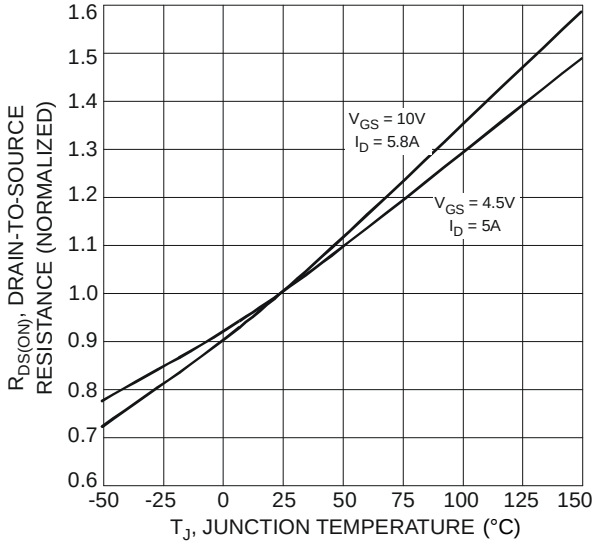


Fig. 5 On-Resistance Variation with Temperature

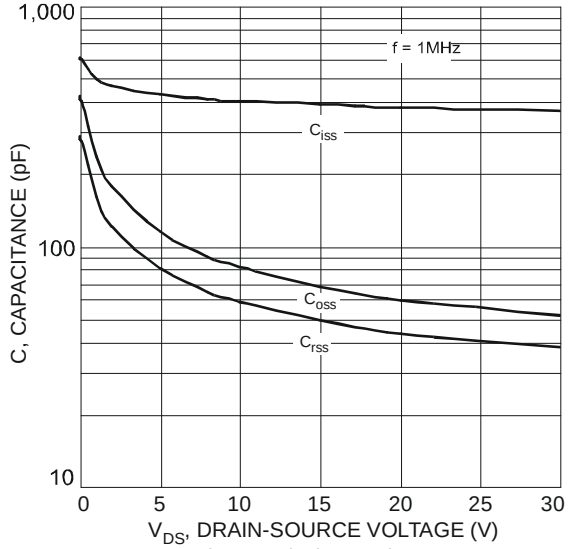


Fig. 6 Typical Capacitance

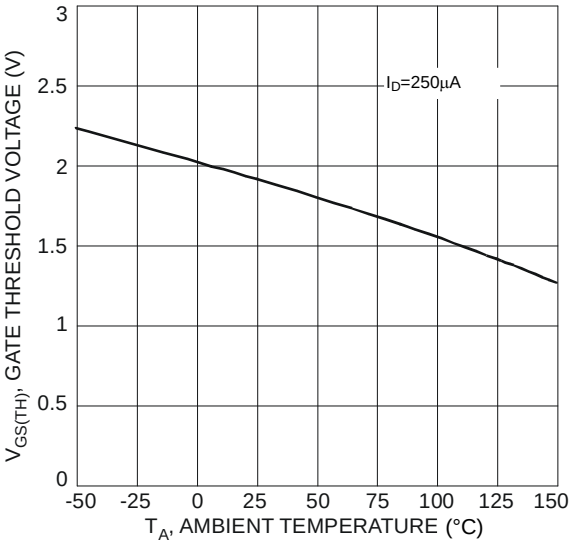


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

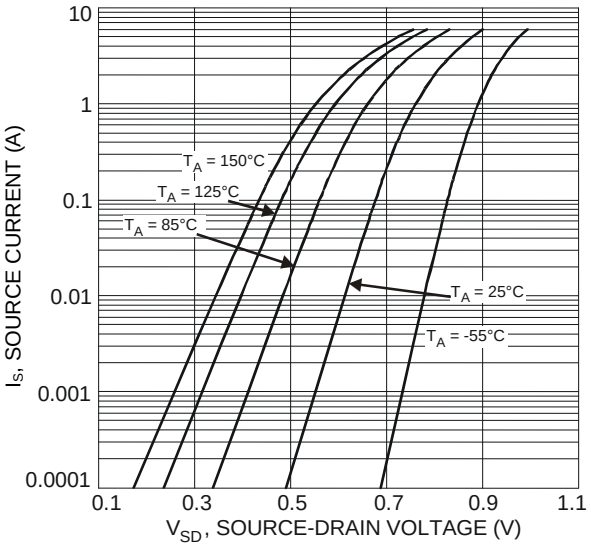


Fig. 8 Diode Forward Voltage vs. Current

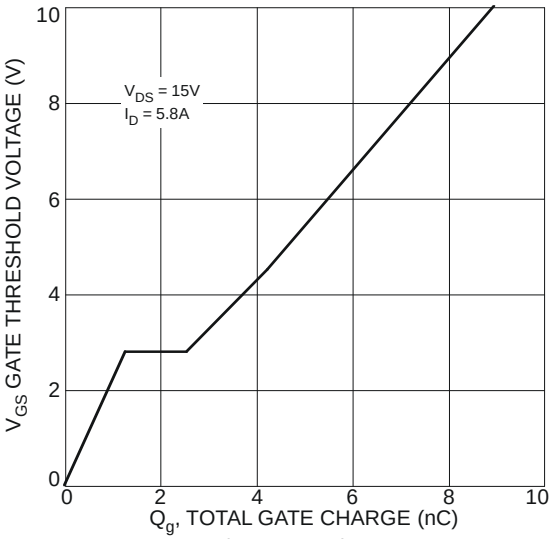


Fig. 9 Gate Charge

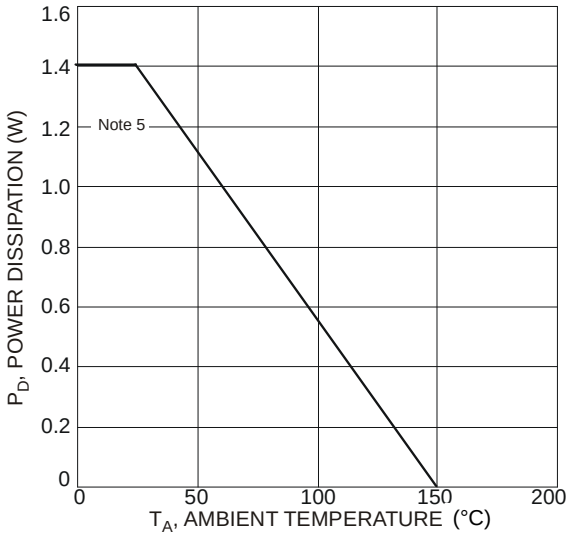


Fig. 10 Power Derating

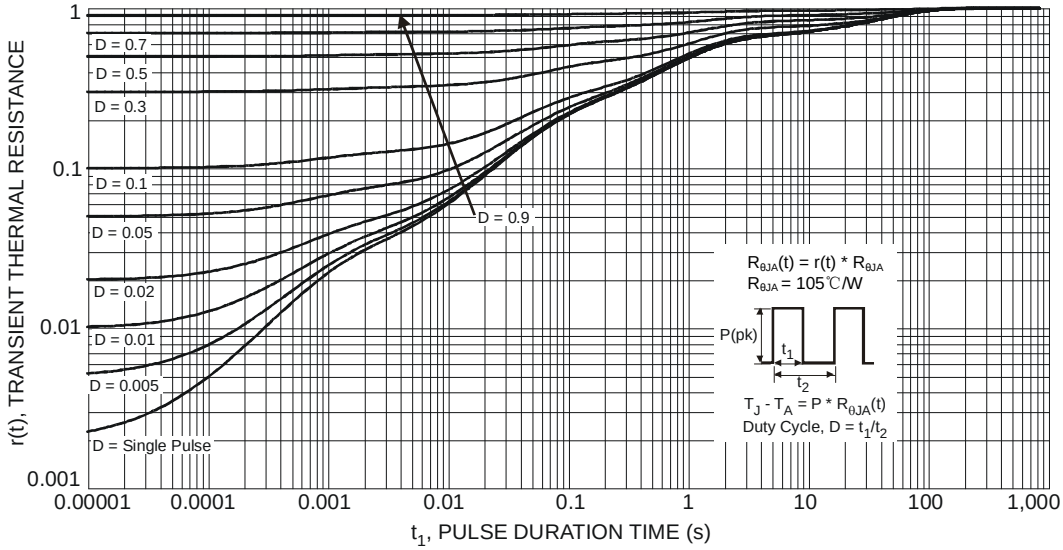
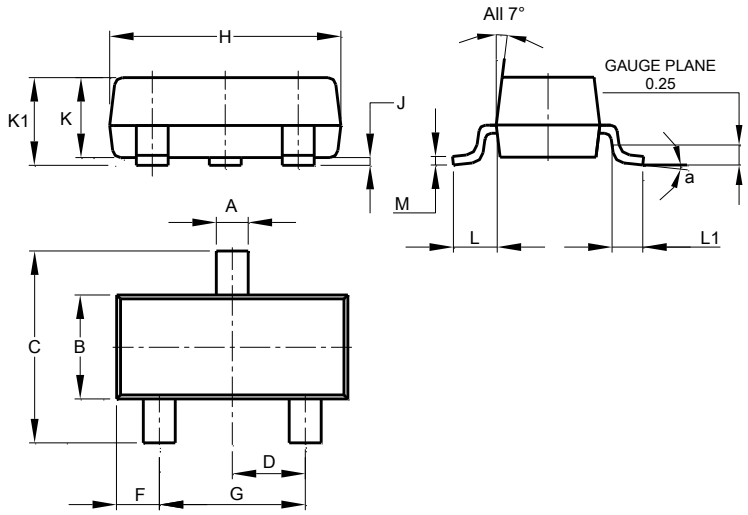


Fig. 11 Transient Thermal Response

Package Outline Dimensions

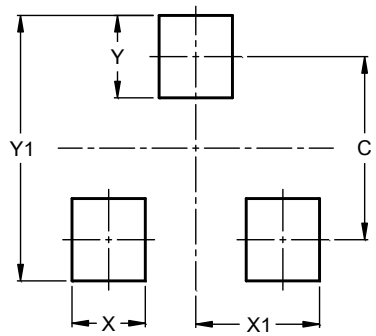
SOT23



SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9